

MICRO ELECTRONICS

PN3568

NPN

SILICON
TRANSISTOR

PN3568 is NPN silicon planar epitaxial transistor designed for amplifier and switching applications for collector current up to 500mA.

TO-92



EBC

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	V _{CB0}	80V
Collector-Emitter Voltage	V _{CE0}	60V
Emitter-Base Voltage	V _{EB0}	5V
Collector Current	I _C	500mA
Total Power Dissipation	P _{tot}	600mW
Operating Junction & Storage Temperature	T _j , T _{stg}	-55 to +150°C

ELECTRICAL CHARACTERISTICS (T_A=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BV _{CB0}	80		V	I _C =100μA I _E =0
Collector-Emitter Breakdown Voltage	LV _{CE0}	60		V	I _C =10mA I _B =0*
Emitter-Base Breakdown Voltage	BV _{EB0}	5		V	I _E =10μA I _C =0
Collector Cutoff Current	I _{CB0}		50	nA	V _{CB} =40V I _E =0
D.C. Current Gain	HFE	40			I _C =30mA V _{CE} =1V*
		40	120		I _C =150mA V _{CE} =1V*
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.25	V	I _C =150mA I _B =15mA*
Output Capacitance	C _{ob}		20	pF	V _{CB} =10V f=1MHz
Current Gain-Bandwidth Product	f _T	60	600	MHz	I _C =50mA V _{CE} =1V

* Pulse Test : Pulse Width = 300μS, Duty Cycle = 2%.

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